

TM100N02D

N-Channel Enhancement Mosfet

General Description

- Low $R_{DS(ON)}$
- RoHS and Halogen-Free Compliant

Applications

- Load switch
- PWM

General Features

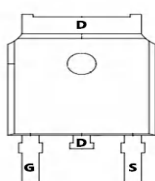
$V_{DS} = 20V$ $I_D = 100A$

$R_{DS(ON)} = 2.6m\Omega (typ.) @ V_{GS} = 4.5V$

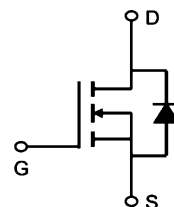
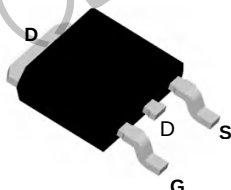
100% UIS Tested
100% R_g Tested



D:TO-252-3L



Marking: 100N02



Absolute Maximum Ratings ($T_C = 25^\circ C$ Unless Otherwise Noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	20	V
V_{GS}	Gate-Source Voltage	± 12	V
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 4.5V$	100	A
$I_D @ T_C = 100^\circ C$	Continuous Drain Current, $V_{GS} @ 4.5V$	69	A
I_{DM}	Pulsed Drain Current	360	A
EAS	Single Pulse Avalanche Energy	118	mJ
I_{AS}	Avalanche Current	41	A
$P_D @ T_C = 25^\circ C$	Total Power Dissipation	88	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient	---	62	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case	---	6.6	$^\circ C/W$

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Electrical Characteristics (T_J=25°C unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	20	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =20V, V _{GS} =0V	-	-	1	μA
I _{GSS}	Gate to Body Leakage Current	V _{GS} = ±12V, V _{DS} =0V	-	-	±100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	0.5	0.7	0.9	V
R _{DS(on)}	Static Drain-Source On-Resistance note3	V _{GS} =4.5V, I _D =30A	-	2.6	3.8	mΩ
		V _{GS} =2.5V, I _D =20A		3.8	4.8	
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} =10V, V _{GS} =0V, f=1.0MHz	-	2200	-	pF
C _{oss}	Output Capacitance		-	460	-	pF
C _{rss}	Reverse Transfer Capacitance		-	445	-	pF
Q _g	Total Gate Charge	V _{DS} =10V, I _D =30A, V _{GS} =4.5V	-	48	-	nC
Q _{gs}	Gate-Source Charge		-	3.6	-	nC
Q _{gd}	Gate-Drain(“Miller”) Charge		-	19	-	nC
Switching Characteristics						
t _{d(on)}	Turn-On Delay Time	V _{DS} =10V, I _D =30A, R _G =1.8Ω, V _{GS} =4.5V	-	9.7	-	ns
t _r	Turn-On Rise Time		-	37	-	ns
t _{d(off)}	Turn-Off Delay Time		-	63	-	ns
t _f	Turn-Off Fall Time		-	52	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I _S	Maximum Continuous Drain to Source Diode Forward Current		-	-	100	A
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	360	A
V _{SD}	Drain to Source Diode Forward Voltage	V _{GS} =0V, I _{SD} =30A, T _J =25℃	-	-	1.2	V
t _{rr}	Reverse Recovery Time	T _J =25℃, I _F =30A,	-	23	-	ns
Q _{rr}	Reverse Recovery Charge	di/dt =100A/μs	-	10	-	nC

Typical Performance Characteristics

Figure 1: Output Characteristics

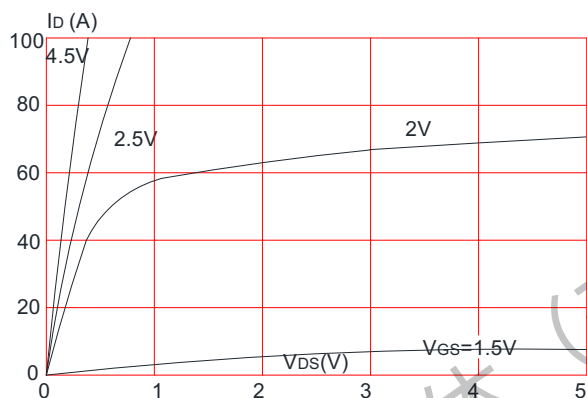


Figure 2: Typical Transfer Characteristics

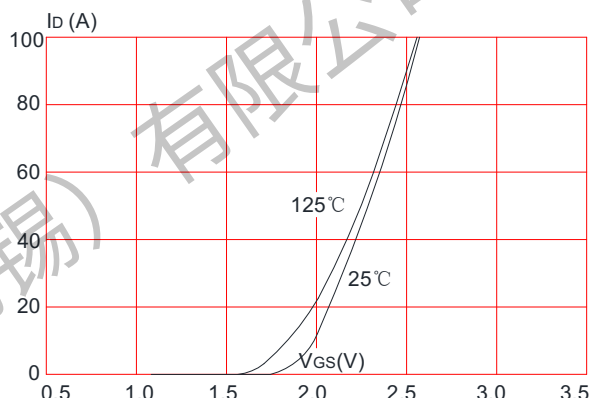


Figure 3: On-resistance vs. Drain Current

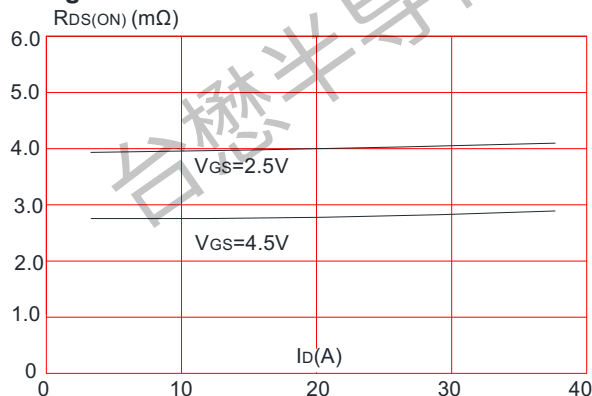


Figure 4: Body Diode Characteristics

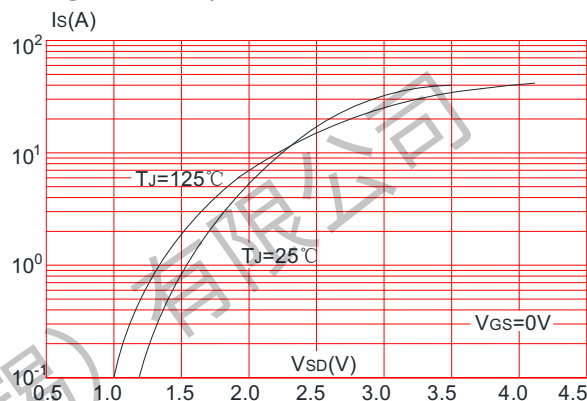


Figure 5: Gate Charge Characteristics

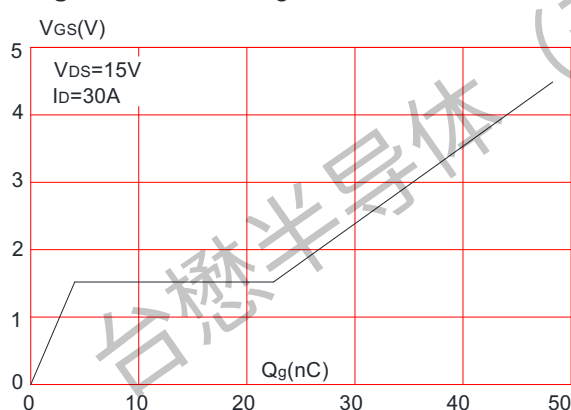
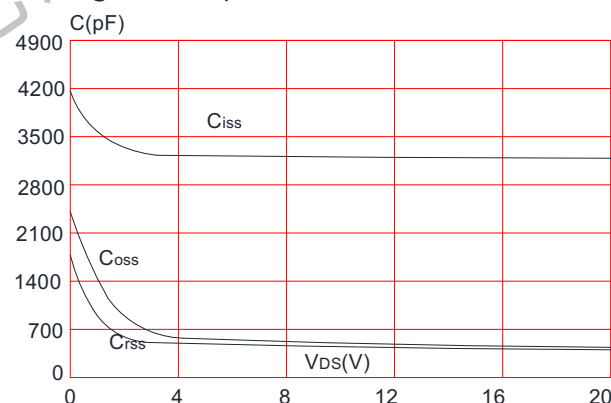


Figure 6: Capacitance Characteristics



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Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

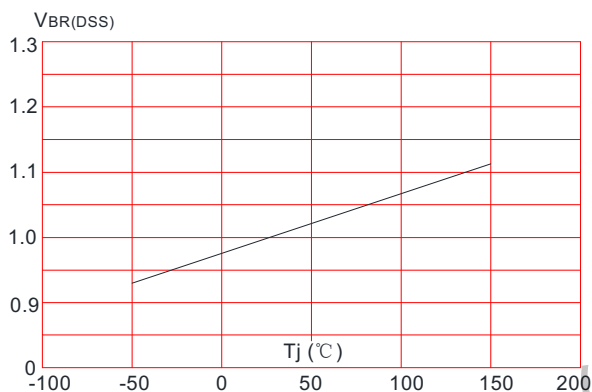


Figure 8: Normalized on Resistance vs. Junction Temperature

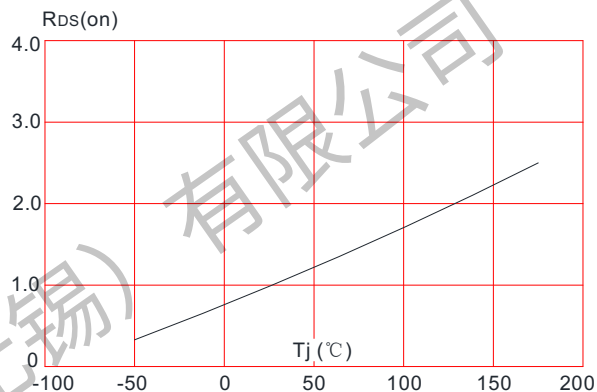


Figure 9: Maximum Safe Operating Area

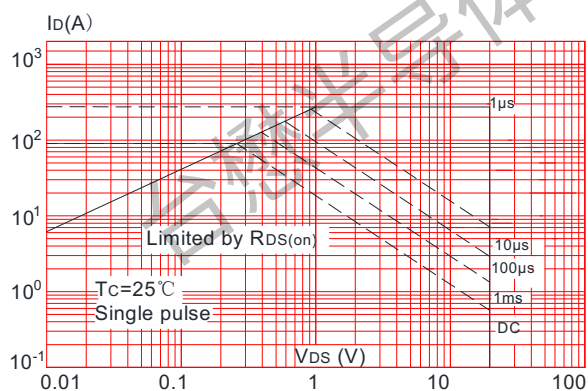


Figure 10: Maximum Continuous Drain Current vs. Case Temperature

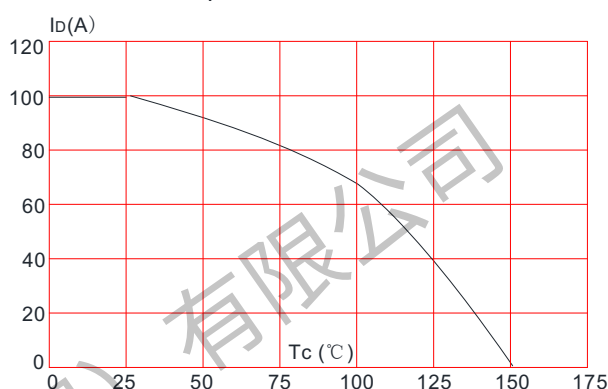
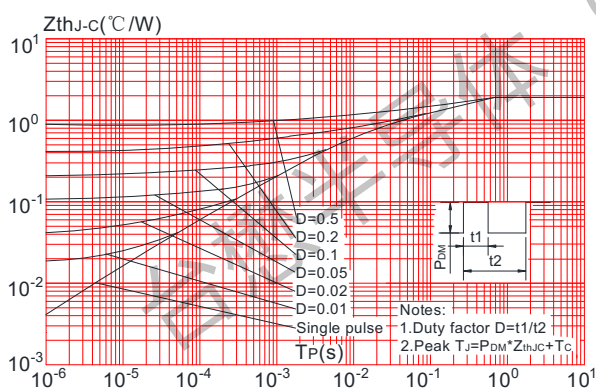
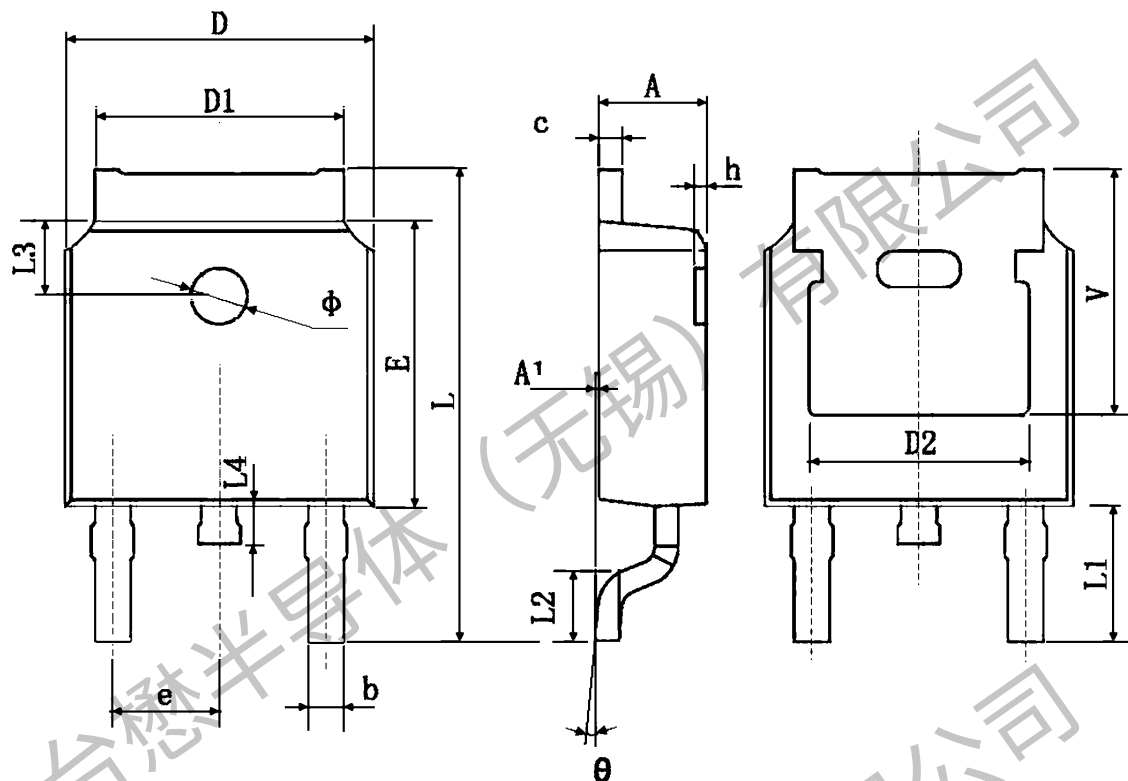


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Case



N-Channel Enhancement Mosfet

Package Mechanical Data: TO-252-3L

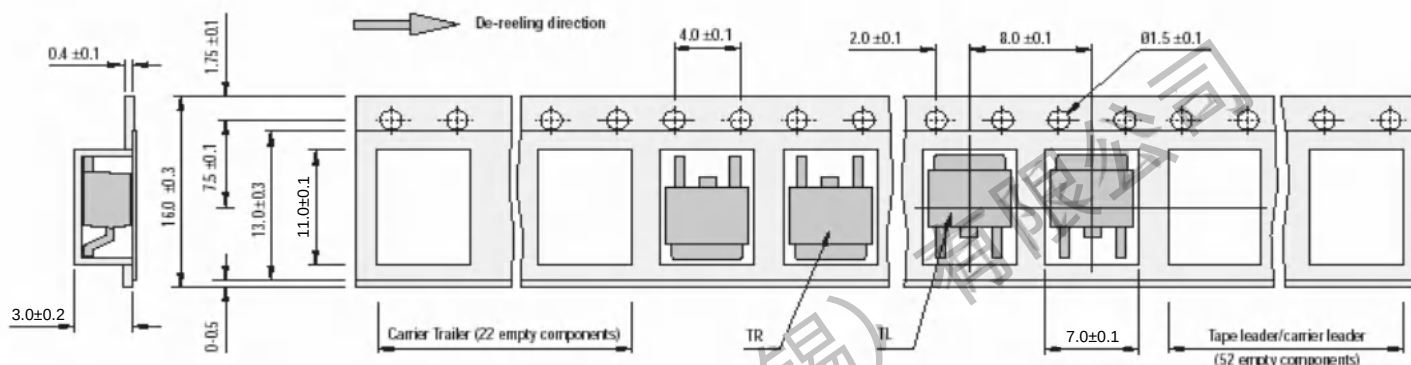


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.660	0.860	0.026	0.034
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	4.830 TYP.		0.190 TYP.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.800	10.400	0.386	0.409
L1	2.900 TYP.		0.114 TYP.	
L2	1.400	1.700	0.055	0.067
L3	1.600 TYP.		0.063 TYP.	
L4	0.600	1.000	0.024	0.039
Φ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.350 TYP.		0.211 TYP.	

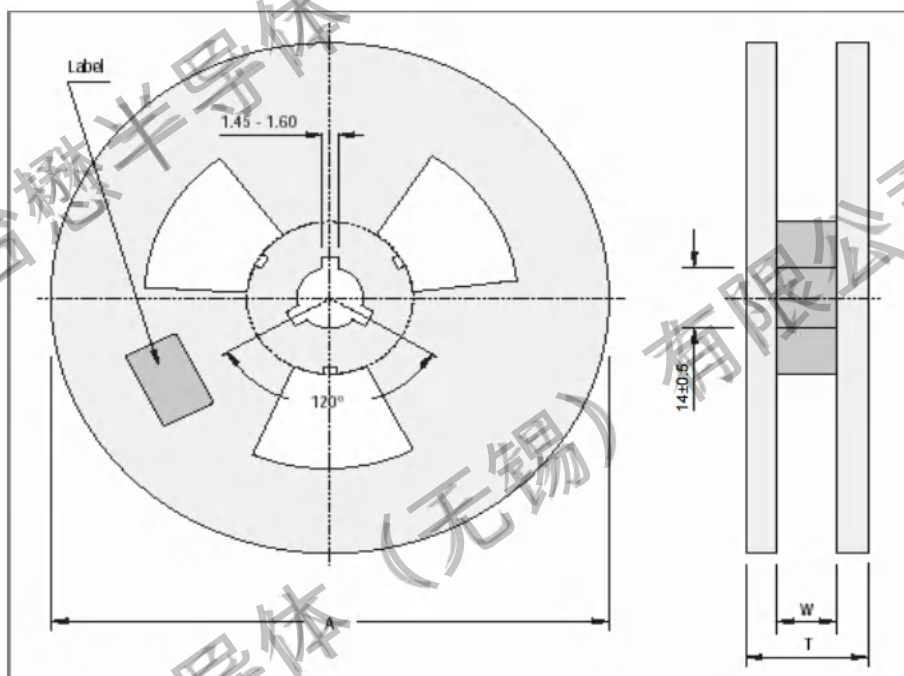
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TO-252-3L Embossed Carrier Tape



TO-252-3L Reel



All Dimensions are in mm

Reel Specifications				
Package	Tape Width	Reel Dia. A - Max	Inside Thickness W	Reel Thickness T - max
TO-252-3L	16	330	18.0 ± 1.5	20

Packaging Information

REEL	Reel Size	Box	Box Size(mm)	Carton	Carton Size(mm)	G.W.(kg)
2,500 pcs	13 inch	5,000 pcs	355×370×50	25,000 pcs	380×275×380	

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Revision history:

Date	Rev	Description	Page
2024.06.11	24.06	Original	